

SEMICONDUCTOR DEVICE HAVING JUNCTION DIODE AND
FABRICATING METHOD THEREFOR

RELATED APPLICATION

5 This application is a divisional of U.S. application serial number 09/645,285, filed
 now Patent No. 6,717,209
on August 24, 2000, which relies for priority upon Korean Patent Application No. 99-
42805, filed on October 5, 1999, the contents of which are herein incorporated by reference
in their entirety.

10 BACKGROUND OF THE INVENTION
FIELD OF THE INVENTION

 The present invention relates to a semiconductor device and a fabricating method
therefor, and more particularly to a semiconductor device having a junction diode and a
fabricating method therefor wherein the junction diode is configured for preventing a gate
15 insulating layer from deterioration arising from a plasma etch process necessary for device
wire layout.

DESCRIPTION OF THE PRIOR ART

 As ULSI semiconductor technology advances, there is an ever-increasing demand
20 for high integration, fine wire and gate patterns, high performance, and wafers of large
diameter and high yield. For this reason, the plasma process has become an indispensable
technology in the field of semiconductor device fabrication.

 Representative examples of plasma processes include the well-known processes of
dry etching, thin layer deposition with plasma CVD, ashing, blanket etch-back and the like.